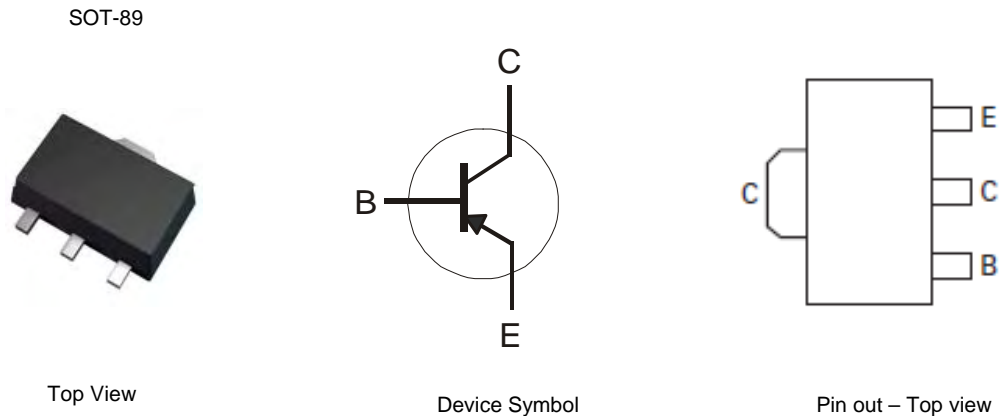


**Features**

- $BV_{CEO} > -32V$
- Max Continuous Current  $I_C = -1A$
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (2DD1664)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free, "Green" Devices (Note 2)**

**Mechanical Data**

- Case: SOT-89
- Case material: molded Plastic. "Green" molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.055 grams (Approximate)

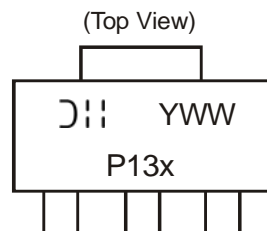


**Ordering Information**

Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
2DB1132P-13	Commercial	P13P	13	12	2,500
2DB1132Q-13	Commercial	P13Q	13	12	2,500
2DB1132R-13	Commercial	P13R	13	12	2,500

Notes: 1. No purposefully added lead.  
2. "Green" devices, Halogen and Antimony Free, Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>

**Marking Information**



P13x = Product Type Marking Code:  
Where P13P = 2DB1132P  
P13Q = 2DB1132Q  
P13R = 2DB1132R  
YWW = Date Code Marking  
Y = Last digit of year ex: 7 = 2007  
WW = Week code 01 - 52

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-32	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Continuous Collector Current	I <sub>C</sub>	-1	A
Peak Pulse Current (Note 4)	I <sub>CM</sub>	-2	A

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient (Note 3)	R <sub>θJA</sub>	125	°C/W
Thermal Resistance, Junction to Leads (Note 5)	R <sub>θJL</sub>	22	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
- 3. For a device surface mounted on FR-4 PCB with minimum suggested pad layout; high coverage of single sided 1 oz copper, in still air conditions
  - 4. Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
  - 5. Thermal resistance from junction to solder-point (at the end of the collector lead).

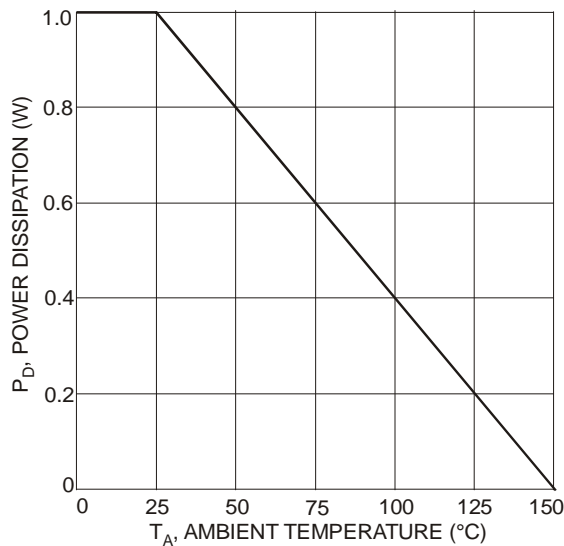


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-40	-	-	V	$I_C = -50\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 6)	$BV_{CEO}$	-32	-	-	V	$I_C = -1\text{mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	-	-	V	$I_E = -50\mu\text{A}$
Collector Cut-off Current	$I_{CBO}$	-	-	-0.5	$\mu\text{A}$	$V_{CB} = -20\text{V}$
Emitter Cut-off Current	$I_{EBO}$	-	-	-0.5	$\mu\text{A}$	$V_{EB} = -4\text{V}$
Static Forward Current Transfer Ratio (Note 6)	$h_{FE}$	82	-	180	-	$I_C = -100\text{mA}, V_{CE} = -3\text{V}$
		120		270		
		180		390		
Collector-Emitter saturation Voltage (Note 6)	$V_{CE(sat)}$	-	-125	-500	mV	$I_C = -500\text{mA}, I_B = -50\text{mA}$
Transition frequency	$f_T$	-	190	-	MHz	$I_E = 50\text{mA}, V_{CE} = -5\text{V}, f = 30\text{MHz}$
Output Capacitance	$C_{ob}$	-	12	30	pF	$I_E = 0\text{A}, V_{CB} = -10\text{V}, f = 1\text{MHz}$

Notes: 6. Measured under pulsed conditions. Pulse width = 300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

**Electrical Characteristics**

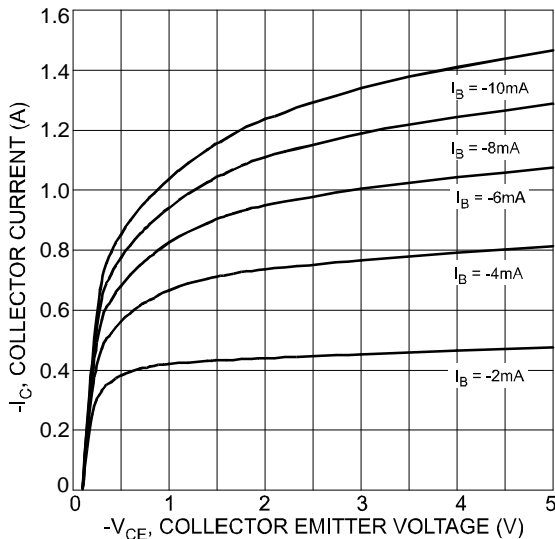


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

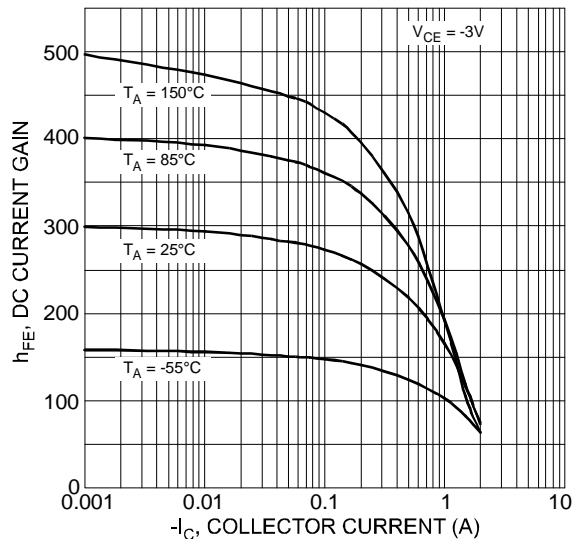


Fig. 3 Typical DC Current Gain vs. Collector Current (2DB1132R)

**Electrical Characteristic - (cont.)**

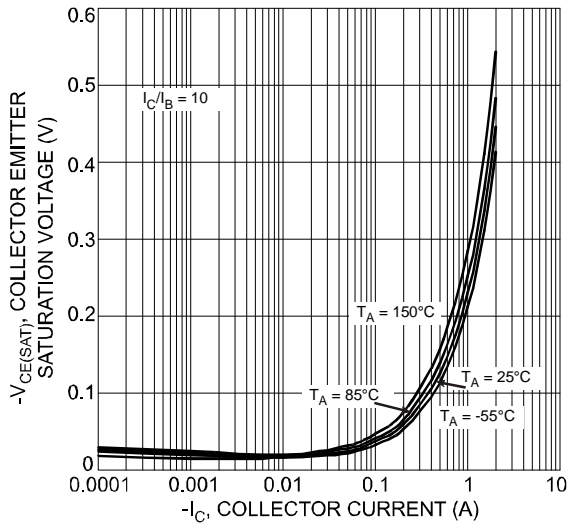


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

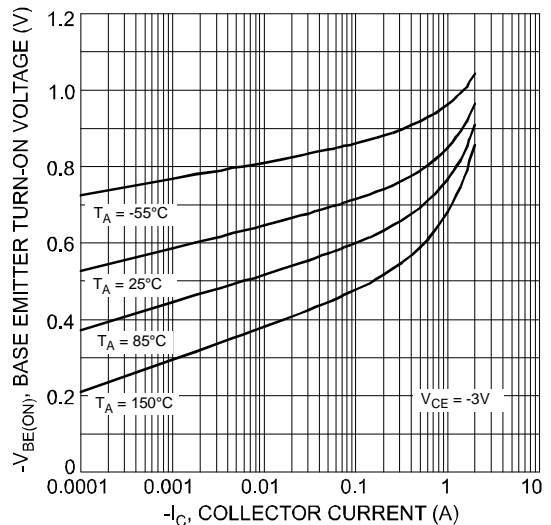


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

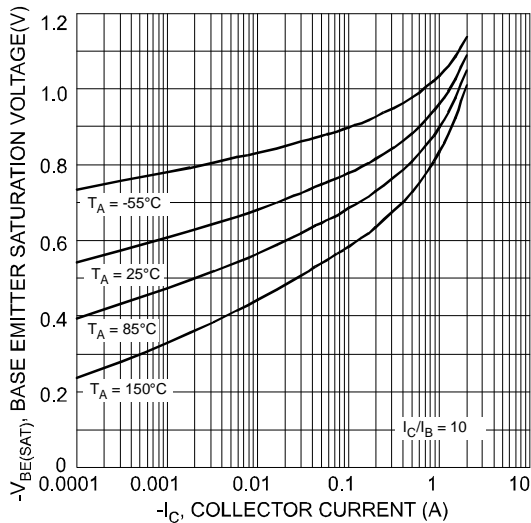


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

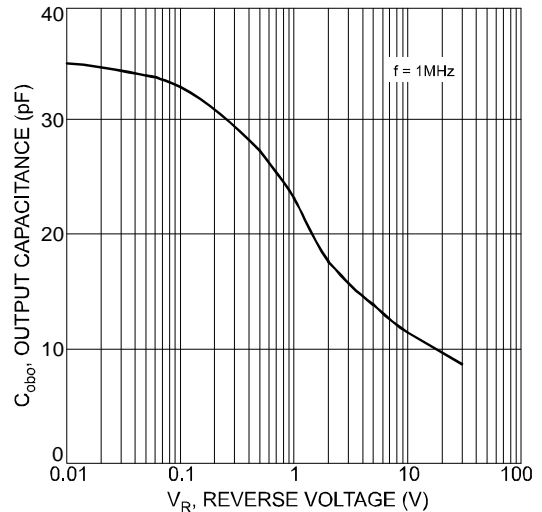


Fig. 7 Typical Output Capacitance Characteristics

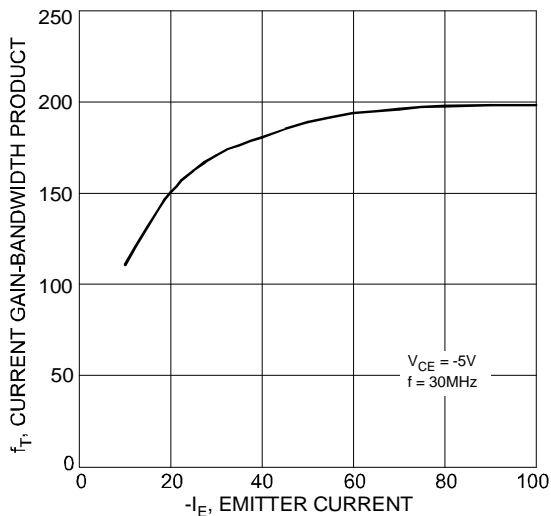
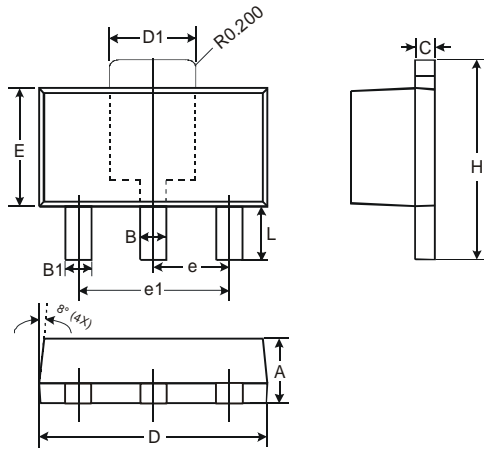


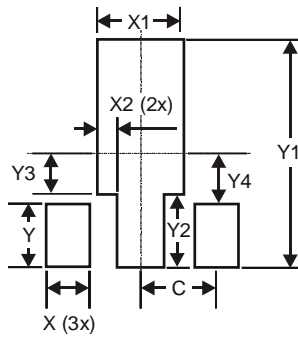
Fig. 8 Typical Gain-Bandwidth Product vs. Emitter Current

**Package Outline Dimensions**



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.43
D	4.40	4.60
D1	1.52	1.83
E	2.29	2.60
e	1.50 Typ	
e1	3.00 Typ	
H	3.94	4.25
L	0.89	1.20
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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